

ABSTRACT

5 The present invention relates to a surface protecting adhesive film for a semiconductor wafer in which an adhesive layer having a storage elastic modulus from 1×10^5 Pa to 1×10^7 Pa at 150 °C and a thickness of from 3 μm to 100 μm is formed on both a surface and back surface of a base film having a melting point of at least 200°C and a thickness of 10 μm to 200 μm . According to the present invention, in a step of grinding the back side of a semiconductor wafer and removing a damaged layer generated on the back side, the semiconductor wafer can be prevented from being broken and being contaminated and the like even if a semiconductor wafer is thinned as low as 100 μm .